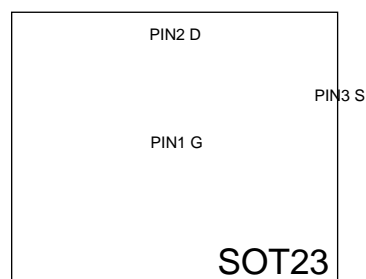


N-Channel MOSFET

$$z V_{DSS}=30\text{ V } I_{D}=3.0\text{ A}$$

$$z R_{DS(on)} < 65\text{ m}\Omega \text{ @ } V_{GS}=9\text{ V}$$

$$z R_{DS(on)} < 78\text{ m}\Omega \text{ @ } V_{GS}=9\text{ V}$$

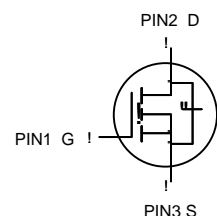


FEATURE

- TrenchFET Power MOSFET

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter



N-Channel MOSFET

Maximum ratings (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J=150^\circ\text{C}$) ^{a,b}	I_D	3.0	A
Pulsed Drain Current	I_{DM}	20	
Continuous Source Current(Diode Conduction) ^{a,b}	I_S	0.62	
Maximum Power Dissipation ^{a,b}	P_D	0.75	W
Thermal Resistance from Junction to Ambient ($t \leq 5\text{s}$)	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

Notes :

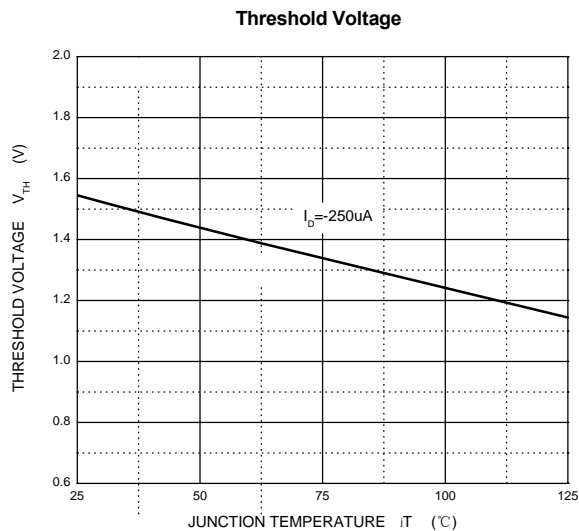
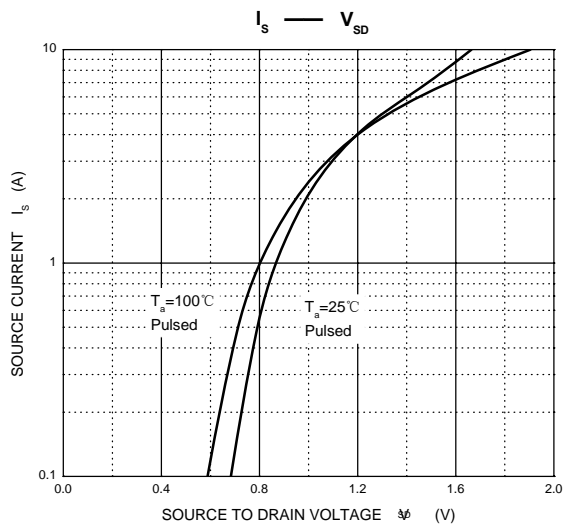
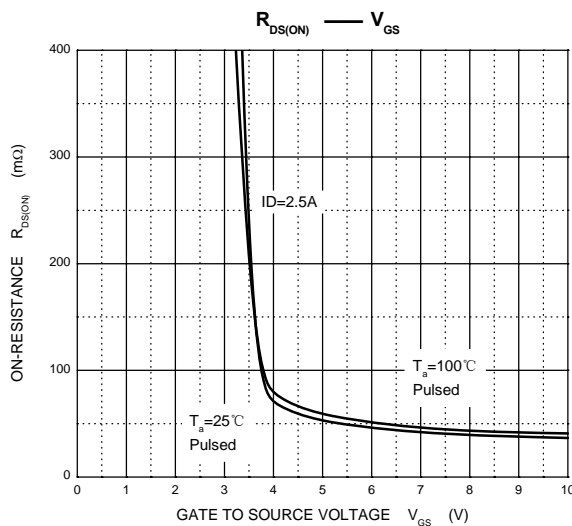
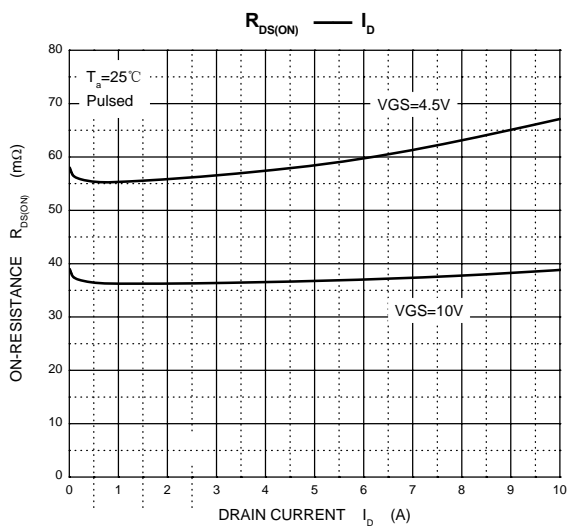
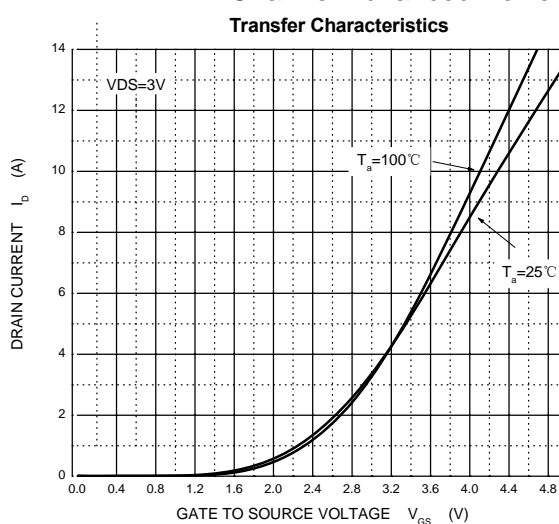
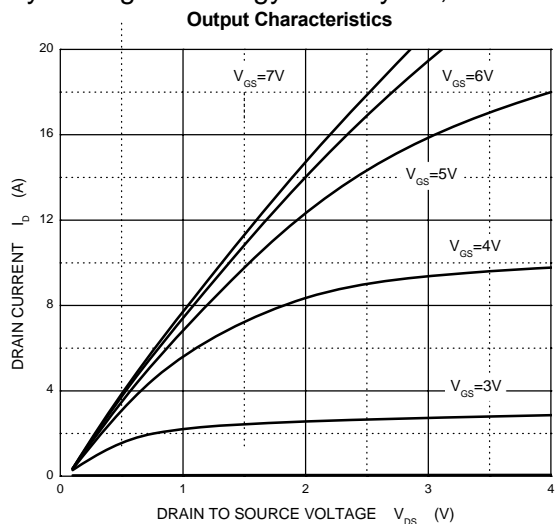
- Surface Mounted on 1" \times 1" FR4 board, $t \leq 5\text{s}$.
- Pulse width limited by maximum junction temperature.

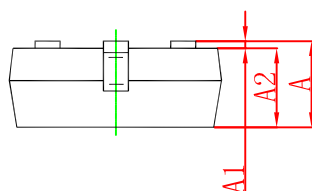
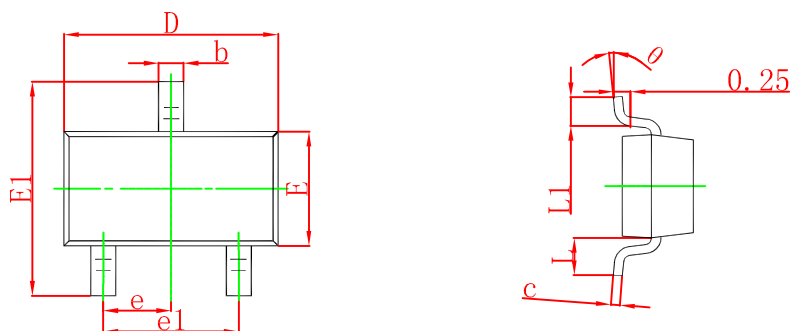
T_a=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DS}	V _{GS} = 0V, I _D =250μA	30			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0		3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} =0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			0.5	μA
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} =10V, I _D =3.0A		55	65	Ω
		V _{GS} =4.5V, I _D =2.0A		66	78	
Forward Transconductance ^a	g _{fs}	V _{DS} =4.5V, I _D =2.5A		7.0		S
Diode Forward Voltage	V _{SD}	I _S =1.25A, V _{GS} =0V		0.8	1.2	V
Dynamic						
Gate Charge	Q _g	V _{DS} =15V, V _{GS} =5V, I _D =2.5A		3.0	4.5	nC
Total Gate Charge	Q _{gt}	V _{DS} =15V, V _{GS} =10V, I _D =2.5A		6	9	
Gate-Source Charge	Q _{gs}			1.6		
Gate-Drain Charge	Q _{gd}			0.6		
Gate Resistance	R _g	f =1.0MHz	2.5	5	7.5	Ω
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f =1MHz		305		pF
Output Capacitance	C _{oss}			65		
Reverse Transfer Capacitance	C _{rss}			29		
Switching						
Turn-On Delay Time	t _{d(on)}	V _{DD} =15V, R _L =15Ω, I _D ≈1A, V _{GEN} =10V, R _g =6Ω		7	11	ns
Rise Time	t _r			12	18	
Turn-Off Delay Time	t _{d(off)}			14	25	
Fall Time	t _f			6	10	

Notes :

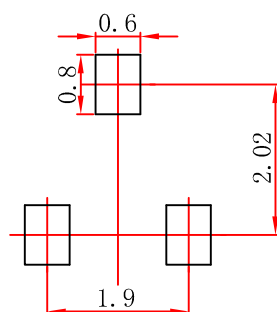
a.Pulse Test : Pulse Width≤300μs, duty cycle ≤2%.





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.